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Switching channels of spin polarized currents in two-dimensional topological insulator

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We study the behavior of spin polarized current in stationary states inside the quantum well described by 2-dimensional Bernevig-Hughes-Zhang model modified by a electric and magnetic barrier inside a non-completly insulating bulk. An attenuated quantum spin Hall effect occurs in the gaped region with a possible like-Klein paradox. Even more interesting, after colliding with the magnetic barrier the returning states eventually revert their spins due spin-momentum locking, giving rise to a spin polarized current in a channel distinct from that of incoming particles of the edge. Because of the time reversal symmetry broken inside the magnetic barrier another channels inside the barrier presents similar effects to a gaped region however preserving couterpropagation with oposite spins.

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Recently, a new class of (topological) state of matter has emerged, named topological insulators (TI's) or quantum spin Hall insulators, they have been predicted to exhibit exotic physical properties depending only on their underlying topology and not on its particular geometry nor mechanical features. For instance, their electronic structure presents a gapless Dirac dispersion, similar to graphene, what make them promising candidates for novel technologies, like in spintronics, because of the strong correlation between spin and momentum, so-called spin-momentum locking, brought about by large spin-orbit coupling in these compounds[1–3]. The two-dimensional topological insulator (2DTI) exhibit a peculiar metallic edge firstly discovered in HgTe/CdTe quantum wells[4]. Indeed, quantum spin Hall insulators are characterized by a full insulating gap in the bulk while their edge states present metallic, chiral, spin polarized, and dissipationless features. Bernevig, Hughes and Zhang developed an effective Hamiltonian, so called BHZ model[6], for describing these special states and they also predicted a quantum phase transition in quantum wells as a function of its thickness, rendering a single pair of helical edge states, for thickness higher than a critical value. Here, we shall consider BHZ model augmented by a step-like barrier, which may mimic a gate-potential, and study its effects on the 2D TI electronic states. Particularly, we realize a channel exchange of the edge current by mean of a energy barrier (like a back-gate) blocking partially and flipping spin of the incident fermions. The fermions which return with spin reversed travel in the opposite direction from the incident current. The effect is duplicated in opposite directions feeding the current in a different channel at the extreme edge where the Dirac mass parameter term (or gap) is zero.

The BHZ model is designed to describe the behavior of charged particles in a CdTe/HgTe sandwich quantum well having a width d. The effective Hamiltonian describing the stationary states inside the well created by the energy difference between the nearest sub-bands of the Fermi level in a inverted regime [7, 8] reads like below:

$$H_0(k) = \begin{bmatrix} \mathcal{H}(k) & 0 \\ 0 & \mathcal{H}^*(-k) \end{bmatrix}, \tag{1}$$

where $\mathcal{H}(k) = \epsilon(k)\mathbf{1}_{2\times2} + \sum_i d_i(k)\sigma_i$, where $\mathbf{1}_{2\times2}$ and σ_i are the identity and the Pauli matrices; $d_1 = Ak_x$, $d_2 = Ak_y$, are the hybridization terms, $d_3 = M - B(k_x^2 + k_y^2)$ is a mass-like term where B and M are known as Newtonian and Dirac mass parameters (more details, below); $\epsilon(k) = C - D(k_x^2 + k_y^2)$. A, B, C, D and M are tunable experimental parameters that depend on the quantum well geometry. C is the minimum energy or Fermi energy near to Γ-point (we normalize energy by taking $C = 0$). We also set $D = 0$ once it has no effect on phase transition and on topological properties; in addition, its vanishing ensures particle-hole symmetry[1]. To study the effects of a step-like potential barrier on the electronic states moving throughout the system, we focus ourselves to the dynamics along x (see Fig.). Once translational symmetry is preserved along y (free motion direction; no barrier), we take $d_2 = 0$ in eq. (1), so that our proposal may be explicitly written as:

$$H_{\text{eff}} = H_0(k_x) + \mathbf{1}_{4\times4}V(x) =$$

$$\begin{bmatrix} \tilde{M}+V(x) & Ak_x & 0 & 0 \\ Ak_x & -\tilde{M}+V(x) & 0 & 0 \\ 0 & 0 & \tilde{M}+V(x) & -Ak_x \\ 0 & 0 & -Ak_x & -\tilde{M}+V(x) \end{bmatrix}, \tag{2}$$

with $\tilde{M} = M - Bk_x^2$, while $V(x) = q\Phi(x)$ is intended to manipulate the energy of the Dirac fermions near the edge (similarly to chemical potential modifying the Fermi

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level) and to create a mechanism for manipulate the attenuation of these particles flowing to a electric and magnetic barrier, for example, by means of a large and continuous gate voltage. This voltage would be applied to a distribution of ferromagnetic metal stripe inside the bulk, suitably located along x-axis. M equals the difference between two energies nearest the Fermi level, $|E_1, +(-)\rangle$ and $|H_1, +(-)\rangle$. If this gap vanishes, what happens at the so-called Γ point, one has two copies of massless Dirac Hamiltonians, with doubly degenerate states, each of them accounting for a given spin polarization. In the absence of the external fields and impurities, M is positive provided that HgTe quantum well thickness, d is smaller than a critical value, $d_c \approx 6,3nm$. In this case, an insulating phase occurs. Whenever d_c threshold is overcome one gets $M < 0$ yielding a conducting phase whose states move on the edges exhibiting spin Hall effect[4, 5, 8].

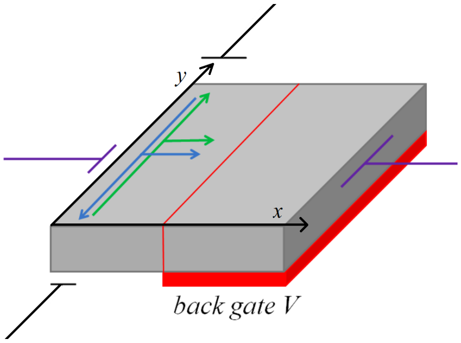

FIG. 1: Schematic illustration of the influence of a back gate for spin up (green arrows) and spin down (blue arrows) currents along the edge direction, axis y, and penetrating through the bulk (shorter arrows), axis-x. The back gate voltage (red region), represented by a step-like barrier, $V(x) = V_0\Theta(x - x_0)$, is intended to split the incident beam into reflected and transmitted currents exhibiting peculiar features like a tunnable energy/momentum filter for incoming particles (see Fig. and related text for details of magnetic effects).

Our main aim is to investigate quantum tunneling effects through a single eletrostatic and magnetostatic barrier in a ($x > x_0$ region) modifying the incident current penetrating through the quantum well (bulk). For doing that, we shall consider a stationary current of particles flowing through the bulk from the left to the right with momentum $\hbar k_x \equiv \hbar k$ and spin up in conduction band (analogously for incident spin down particles in valence band), as follows:

$$\Psi_i^{\uparrow} = \mathcal{A}_i\, e^{kx} \left[\begin{array}{c} 1 \\ \frac{Ak_1}{E+M(k_1)} \\ 0 \\ 0 \end{array} \right] . \tag{3}$$

This solution depends only on the experimental parameters of the BHZ model and the amplitudes are determined by normalization and boundary conditions. We choose a incident wave incoming from the right side to the left so that the wavenumber is the coefficient k, related with the experimental parameters as $k = \frac{1}{2B}(A + i\sqrt{4MB - A^2})$. We propose a theoretical situation where $4MB > A^2$, enabling an attenuated and oscillatory solution in the bulk. After solving the eigenvector problem:

$$H_{\text{eff}}(k_x \to i\partial_x - q\vec{A})\Psi(x) = (E - V(x))\Psi(x) \, . \tag{4}$$

Adopting Landau gauge in the barrier region, $\vec{A} = (0, A_y, 0)$, where $A_y(x) = \Theta(x - x_0)B_z x$, we have a perpendicular magnetic field permeating the thin film in $x > x_0$. The eingenstates describe opposite spins related by time reversal symmetry (TRS), $\mathcal{T}\Psi_{\uparrow}(x) = \Psi_{\downarrow}(x)$. For the two different regions inside the bulk, say, outside ($x \le x_0$) and inside the barrier, $x \ge x_0$ we obtain the reflected (r) and transmitted (t) solutions as below:

$$\Psi_r = \mathcal{A}_r^{\uparrow} e^{-kx} \left[\begin{array}{c} 1 \\ \frac{-Ak_1}{E+M(k_1)} \\ 0 \\ 0 \end{array} \right] , + \mathcal{A}_r^{\downarrow} e^{-kx} \left[\begin{array}{c} 1 \\ \frac{-Ak_1}{E+M(k_1)} \\ 0 \\ 0 \end{array} \right] , \tag{5}$$

$$\Psi_t = \mathcal{A}_t^{\uparrow} e^{k'x} \left[\begin{array}{c} 1 \\ \frac{Ak_2}{E-V_0+M(k_2)} \\ 0 \\ 0 \end{array} \right] , + \mathcal{A}_t^{\downarrow} e^{k'x} \left[\begin{array}{c} 1 \\ \frac{Ak_2}{E-V_0+M(k_2)} \\ 0 \\ 0 \end{array} \right] , \tag{6}$$

with $k = a + ik_1$ and $k' = a' + ik_2$, where $a < 0$ and $a' < 0$. The incoming, reflected and transmited solution yield the combined spinor:

$$\Psi(x) = \theta(-x)[\Psi_i^{\uparrow}(x) + \Psi_r^{\uparrow}(x) + \Psi_r^{\downarrow}(x)] + \theta(x)[\Psi_t^{\uparrow}(x)\Psi_t^{\downarrow}(x)] \tag{7}$$

By mean of boundary conditions in $x = x_0$, we calculate the normalization factors leading to relations: $\mathcal{A}_i = (1 + \Omega)\mathcal{A}_t$ and $2\mathcal{A}_r = (1 - \Omega)\mathcal{A}_t$. Their associated average currents may be calculated by the standard quantum mechanical procedure, $J_x = \Psi^{\dagger}\frac{\partial H_0(k_x)}{\partial x}\Psi$, and read explicitly:

$$J_i = 2|\mathcal{A}_i|^2 \left\{ Bk_1 + \frac{A^2 k_1}{E + \tilde{M}(k_1)} + \frac{BA^2 k_1^3}{[E + \tilde{M}(k_1)]^2} \right\} e^{2|a|(x+x_0)} \quad (x \le 0), \tag{8}$$

$$J_r = 2|\mathcal{A}_r|^2 \left\{ Bk_1 + \frac{A^2 k_1}{E + \tilde{M}(k_1)} + \frac{BA^2 k_1^3}{[E + \tilde{M}(k_1)]^2} \right\} e^{2|a|(x+x_0)} \quad (x \le 0), \tag{9}$$

$$J_t = 2|\mathcal{A}_t|^2 \left\{ Bk_2 + \frac{A^2 k_2}{E + \tilde{M}(k_2)} + \frac{BA^2 k_2^3}{[E + \tilde{M}(k_2)]^2} \right\} e^{-|a'|(x+x_0)} \quad (x \ge 0) \, , \tag{10}$$

yielding reflectance and transmittance factor like below:

$$R = \frac{|1-\Omega|^2}{|1+\Omega|^2} e^{-4|a|x-x_0} \ (x \le 0), \tag{11}$$

$$T = 4\frac{k_2}{k_1}\frac{E+M(k_1)}{E+M(k_2)-V_0}\frac{e^{2(a-a')x-x_0}}{|1+\alpha|^2}, \ (x \ge 0), \tag{12}$$

where $\Omega = \frac{k'}{k}\frac{E+M(k_1)}{E+M(k_2)-V_0}$.

By tuning the electrostatic potential $V_0 = q\Phi$ one can obtain three distinct scenarios depending on the relative value of the 'net energy', $E + M(k_2) - V_0$. The particle-hole symmetry can be modified if we have V_0 once the hole solution Thus, a weak potential $V_0 < E + M(k_1)$ leads small attenuation, once $a \sim a'$. (If $V_0 \ll E$ we have $l_t \approx |B/3A|$) With a medium value of the potential, $E - M(k_1) < V_0 < E + M(k_1)$, the wavenumber inside the barrier, k_2, becomes pure imaginary, modifying the transmitted current and hence the transmittance. Thus, the decay length of edge states inside the barrier is $l_t = \frac{1}{|a'-k_2|}$. In this particular case $k' = a' - k_2$ is a real number. For this reason, the wave inside the barrier is completely attenuated, i.e., solutions of the wave equation in this region has not oscillatory part, only in the region $x < 0$, near the edge.

A strong potential, $V_0 > E + M(k_1)$, yields to a peculiar oscillatory regime regarded (with $A^2 < 4MB$). Some consequences of a non completely insulating bulk or/and a semiconductor bulk are related to dependence of k and the experimental parameters. k_1 is real and it must be positive, which leads to a negative sign for the ratio k_2/k_1 and hence the transmission coefficient, T, becomes negative like a paradox Klein with attenuation, therefore, we assume that $a \ne 0$ and $a' \ne 0$. Even in this case, there is a current of holes with inverted spins associated with negative energy, implying massive fermions of valence band, contributing to currents also.

The dispersion relations read, respectively:

$$\begin{cases} A^2k_1^2 = E^2 - M^2(k_1) & \text{(inside barrier)} \\ A^2k_2^2 = (E-V_0)^2 - M^2(k_2) & \text{(outside barrier).} \end{cases} \tag{13}$$

In Fig. we plot dispersion relations for three distinct cases according to the relative V_0-value to $E - M(k_2)$.

The group velocity decrease according the distance to extreme edge, $v_g = \pm\frac{A}{\hbar}\sqrt{1 - A^2/4MB} \leqslant v_{edge} = |A|/\hbar$. Phase velocities outside and inside the eletrostatic barrier are respectively: $v_{f1}^2 = (E^2 - \tilde{M}^2(k_1))/\hbar^2|k_1|^2$; $v_{f2}^2 = (E-e\Phi)^2 - \tilde{M}^2(k_1))/\hbar^2|k_2|^2$

Supondo uma barreira com um campo magnetico uniforme e constante na regiao x ¿0, a hamiltoniana se torna:

$$H_{\text{eff}}(k_x \to i\partial_x - q\vec{A})\Psi(x) = E\Psi(x)\,, \tag{14}$$

where $\vec{A} = (0, A_y, 0)$, $A_y(x) = \theta(x - x_0)B_z$

poderemos ter uma corrente com spins invertidos devido ao acoplamento mnimo na hamiltoniana que quebra a reversao temporal trazendo solucoes com spin down nas ondas refletidas e transmitidas:

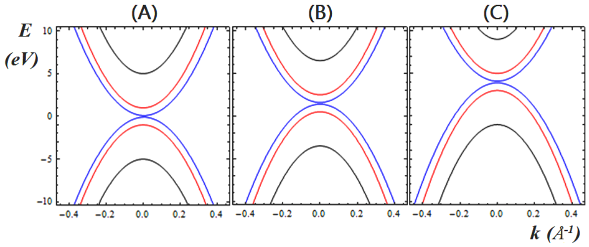

FIG. 2: Sketch of dispersion of the massive particles with different parameters values. Zero-energy is taken to be the Fermi level. A) Without the potential barrier; (B) With a typical value of the energy barrier ≈ 1eV; (C) With a higher value of the energy barrier $V_0 > E + M(k_1)$. Black, red and blue curves represent higher, intermediary, and low gaps. Higher separation of the bands (higher gap) implies few particles and small velocities inside the bulk and inside barrier.

$$\Psi_r^{\downarrow} = \mathcal{A}_r e^{-kx} \begin{bmatrix} 1 \\ \frac{-Ak_1}{E+M(k_1)} \\ 0 \\ 0 \end{bmatrix}, \Psi_t^{\downarrow} = \mathcal{A}_t e^{k'x} \begin{bmatrix} 1 \\ \frac{Ak_2}{E-V_0+M(k_2)} \\ 0 \\ 0 \end{bmatrix}, \tag{15}$$

the transmited wave with spin up also is modified duo magnetic field in a region $x > x_0$:

$$\Psi_t^{\uparrow} = \mathcal{A}_t^{\uparrow} e^{k'(x-x_0)} \begin{bmatrix} 1 \\ \frac{A(k_2+eA_y/\hbar)}{E-V_0+\tilde{M}(k_2,A_y)} \\ 0 \\ 0 \end{bmatrix}. \tag{16}$$

The combined spinor solution is:

$$\Psi(x) = \theta(-x)[\Psi_i^{\uparrow}(x) + \Psi_r^{\uparrow}(x) + \Psi_r^{\downarrow}(x)] + \theta(x)[\Psi_t^{\uparrow}(x)\Psi_t^{\downarrow}(x)] \tag{17}$$

The dispersion are similar making a substituition of minimal coupling.:

There are spin up reflected and transmited solutions in this case:

The conductivity of the edge increases according to the potential in relation to incident energy of fermions. Those fermions returning with inverted spins, illustrated in fig. , travel in the opposite direction from the incident current and may be more easily detected in the regime $A^2 < 4MB$, because the fermions flow distances greater than $A^2 \ge 4MB$ case. Meantime, effects of destructive interference of the wavefunctions of the incoming and returning fermions tend to diminish the refeeding currents. However, different amplitudes, spins and different paths to channels may avoid this for equal fermions, at first. In our proposal, the phase of wavefunction is modified according the gain or loss of mass and the effect appears to

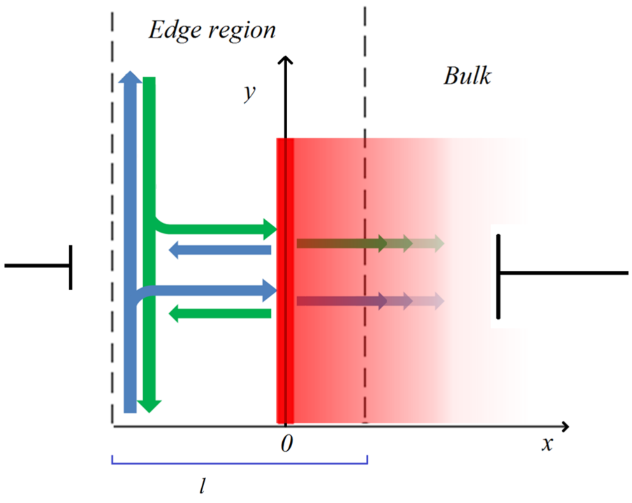

FIG. 3: Illustration of the spin up (green) and spin down (blue) currents leaving and returning from the edge. The red rectangle represents the step-potential and l is the decay length of edge states without barrier influence. The reflected currents have reverted spins and feed the zero-gap currents in the the edge again, increasing the conductivity in a different channel.

be robust due to an electrical potential difference transverse to the edge guiding the current into the semiconductor bulk.

The case of a symmetrical quantum well, with a second step-barrier in opposite side of the first, may be investigated in the same way. The solutions are analogous but with different directions of attenuation. If we ignore a second reflection at the barriers, because the attenuation prevents the confinement, there is a more symmetrical situation and no influence of SIA term. Thus these consequences of the quantum spin Hall effect by applying, for example, an electric field in regions near the edge in large quantum wells, when $A^2 < 4MB$. Such a proposal is namely possible provided that B increases (and A decreases) as the thickness d gets higher, as expected from experiments [8].

Unlike a conductor, or an usual insulator, we would have, a static electric field or a large impurity as a large and incontournable barrier forbidding particles returning without inversion of the spin. Once current is conserved, $J_i + J_r = J_t$, the inverted-spin massive current feeds the edge current, losing mass returning to the edge channel. Our proposal, illustrated in figure , performed recent spin detection in polarized currents in Refs. [9, 10], once our interest is focused on the bulk currents.

On the other hand, in the regime $A^2 < 4MB$, with small dissipation, the spin may be flipped using a non-magnetic barrier in the bulk. It would be possible to construct spintronic devices controlling the voltages to direct the egde currents like the Ref [10], but also the transverse voltage of our proposal which enable the edge current to collide with the barrier inside the bulk, modifying the information of spin at extreme edge and create a measurable mechanism.

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